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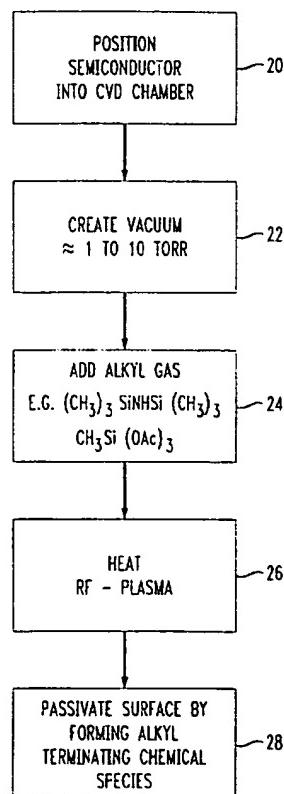
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(54) Surface treatment anneal of silicon-oxy-carbide semiconductor surface layer

(57) A method of surface treating a semiconductor surface and semiconductor article is disclosed. A deposited semiconductor surface layer is treated and annealed within an alkyl environment of a chemical vapor deposition chamber to passivate the semiconductor surface layer by bonding with the silicon and attaching alkyl terminating chemical species on the surface of the semiconductor surface layer to aid in dehydroxylating the surface. The semiconductor surface layer comprises a polysilicon-oxy-carbide surface layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0.

FIG. 1



Description**Field Of The Invention**

[0001] This invention relates to the passivation of semiconductor surfaces, and more particularly, this invention relates to a method of treating a silicon-oxy-carbide semiconductor surface layer to dehydroxylate the surface.

Background Of The Invention

[0002] Parasitic capacitance is a problem when inter-metal dielectrics are used for semiconductor surface layers or substrates. Greater use of silicon substrates or surface layers that are formed with the addition of other elements, such as oxygen and carbon, is becoming more commonplace to reduce parasitic capacitance. A substantial portion of the carbon atoms are intermixed and some are bonded with the silicon. One area of interest has been the use of different types of silicon-oxy-carbide glass and the associated methods to form a semiconductor surface layer.

[0003] Much study has already been accomplished with the use of the reactions between silicon, carbon and oxygen, especially for the use of "nicalon" fibers and composite ceramics. Some of these products have been used in fiber optic applications. An example is the silicon-oxy-carbide glass method of preparation and associated product disclosed in U.S. Patent No. 5,180,694 to Renlund et al., the disclosure which is hereby incorporated by reference in its entirety. It has been found that these types of materials can also be used in the semiconductor industry.

[0004] These low dielectric constant (low k) inter-metal dielectrics are applicable with silicon-oxy-carbide glass and reduce parasitic capacitance. Amorphous, hydrogenated silicon-oxy-carbide (-SiOC:H) has been found to be a viable low k material for advanced integrated circuit technology applications, such as with copper. Chemical vapor deposition (CVD) of -SiOC:H glass from a mixture of alkyl-silane and nitrous-oxide has a dielectric constant (k) of about 2.5 to 3.0, as compared to conventional SiO₂ with a dielectric constant 3.9. The k value of the -SiOC:H film is directly proportional to the carbon content where a higher carbon content yields a lower k. A higher carbon content creates problems with conventional lithography pattern transfer because of a reduced chemical etch selectivity between the -SiOC:H and the polymer photo resist material. Another prior art method for reducing the dielectric constant (k) is to make it porous, basically encapsulating voids in the -SiOC:H film. This results in a suitable low k film, with a carbon content of about 5-20 atomic percent. However, dangling bonds exist along the void surface. These dangling sites cause the film's dielectric properties to be unstable.

[0005] Prior art attempts to correct the unstable dielectric properties have included the excessively long

curing in oxygen and/or nitrogen, or capping the -SiOC:H film with a barrier, such as silicon nitride. The long cure (2-5 hours) is expensive in terms of cycle time and additional facility requirements. Furthermore, the films

5 are not completely stable because bond sites are not fully pacified. The barrier films have a higher dielectric constant (typically >4.0) which increases the effective k.

[0006] There has been some chemical treatment for silica-containing glass surfaces using strained siloxane 10 rings, such as disclosed in U.S. Patent No. 5,965,271 to Grabbe et al., the disclosure which is hereby incorporated by reference in its entirety. However, the '271 disclosure is directed to a more conventional silica-containing glass surface and not the silicon-oxy-carbide semiconductor surface layer as in the present invention.

Summary of the Invention

[0007] It is therefore an object of the present invention 20 to passivate a deposited polysilicon-oxy-carbide surface layer to dehydroxylate the surface without impairing its function.

[0008] The present invention cures the -SiOC:H layer 25 in an alkyl environment, thus effectively changing the Si-OH, SiH and Si-O into Si₃(CH₃)₃. This passivation cure is performed insitu in a plasma enhanced (PE-) CVD reactor by dissociating methane, acetylene or any other alkyl component, such as hexamethyldisilane (HMDS) or methyltriacetoxysilane (MTAS).

[0009] In still another method aspect of the present invention, the semiconductor surface layer deposited over a semiconductor substrate is treated in an alkyl environment. The semiconductor surface layer comprises a deposited polysilicon-oxy-carbide layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0. The method comprises the steps of positioning the semiconductor substrate within a chemical vapor deposition chamber and heating the surface layer. The 35 surface is annealed within an alkyl environment of the chemical vapor deposition chamber to passivate the semiconductor surface layer while bonding with the silicon an attaching alkyl terminating chemical species on the semiconductor surface layer to aid in dehydroxylating the surface.

[0010] The step of heating further comprises the step 40 of heating with a plasma within the chemical vapor deposition chamber. The heating step with a plasma can occur at a power of about 100 to about 500 watts. A radio frequency induced current can be generated and typically is about 12 to about 14 MHz. The annealing can occur within a vacuum environment of about 1 to about 10 Torr.

[0011] In still another aspect of the present invention, 45 a semiconductor article includes a semiconductor substrate and deposited polysilicon-oxy-carbide surface layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric con-

stant of about 2.5 to about 3.0. A passivating surface layer has a terminating chemical species that is substantially free of hydroxyl and formed by heating the polysilicon-oxy-carbide surface layer within a chemical vapor deposition chamber and contacting the surface with an alkyl to bond molecules via Si-O-Si chains and dehydroxylate the surface. The alkyl group in one aspect of the present invention can be selected from the group consisting of: acetylene, methane, hexamethyldisilane and methyltriacetoxysilane to bond molecules via Si-O-Si chains and dehydroxylate the surface. The hexamethyldisilane and the methyltriacetoxysilane are about 1% to about 30% concentration.

Brief Description Of The Drawings

[0012] Other objects, features and advantages of the present invention will become apparent from the detailed description of the invention which follows, when considered in light of the accompanying drawings in which:

[0013] FIG. 1 is an overall flow chart showing the sequence of steps used for treating the polysilicon-oxy-carbide surface layer in accordance with the present invention.

[0014] FIG. 2 is a schematic drawing showing a polysilicon-oxy-carbide semiconductor surface layer that has an alkyl anneal to fill voids and dehydroxylate the surface.

[0015] FIG. 3 is a schematic drawing showing the annealing of a polysilicon-oxy-carbide surface layer with hexamethyldisilane.

[0016] FIG. 4 is a schematic drawing showing the annealing of the polysilicon-oxy-carbide semiconductor surface layer with methyltriacetoxysilane.

[0017] FIG. 5 is a schematic, side sectional view of a chemical vapor deposition chamber that can be used with the present invention.

Detailed Description Of The Preferred Embodiments

[0018] The present invention is advantageous because it now allows the curing of an -SiOC:H, silicon-oxy-carbide semiconductor surface layer in an alkyl environment to allow the passivation of the Si-OH, SiH and Si-O as $\text{Si}_5(\text{CH}_3)_3$. The passivation cure is performed insitu in a plasma enhanced (PECVD) reactor by dissociating methane, acetylene or any other alkyl component, such as hexamethyldisilane (HMDS) or methyltriacetoxysilane (MTAS).

[0019] Typically, the semiconductor surface layer of the present invention comprises a polysilicon-oxy-carbide surface layer 10 deposited over a semiconductor substrate or other base 12 (FIG. 2). The polysilicon-oxy-carbide material could be the substrate for subsequent layering. The polysilicon-oxy-carbide (-SiOC:H) has a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5

to about 3.0. Although 5% to about 20% typically is the range of carbon content, it is possible to have a carbon content as high as 40% in special cases. However, a 40% carbon concentration is not as desirable because it becomes more difficult to integrate the semiconductor surface layer with the other processes.

[0020] FIG. 1 illustrates the basic method of the present invention where at block 20, the semiconductor substrate 10 has a silicon-oxy-carbide surface layer 12 of the present invention and is positioned into a chemical vapor deposition chamber. Typically the substrate 10 and surface layer 12 are formed as a wafer (FIG. 5). Naturally, one or more wafers can be placed into a chemical vapor deposition chamber and it is typical that a large plurality of wafers are placed into a chamber as shown in the chemical vapor deposition chamber 16 of FIG. 5.

[0021] A vacuum is created, typically on the order of about 1 to 10 Torr as shown in block 22. An alkyl environment is created within the chemical vapor deposition chamber by injecting the alkyl gas. Although many different types of alkyls can be used, acetylene, methane, hexamethyldisilane, $(\text{CH}_3)_3\text{SiNHSi}(\text{CH}_3)_3$ and methyltriacetoxysilane, $\text{CH}_3\text{Si}(\text{OAC})_3$ are advantageous. A plasma is created to heat the semiconductor surface layer 12, such as with a radio frequency that creates a plasma (block 26). The surface layer is passivated by forming an alkyl terminating chemical pieces (block 28). It is not desirable to heat above 450 to 500 C. In order to break the molecules of the alkyl and break the hydroxide groups formed on the voids of the semiconductor layer, it is often necessary to induce the plasma with a radio frequency power as is well known to those skilled in the art. Typically the plasma power is about 100 to about 500 watts. Typical flow of an alkyl material will be on the order of about a liter per minute, usually sufficient enough to fill in the pores that are originally formed in the semiconductor silicon-oxy-carbide surface layer.

[0022] FIG. 2 illustrates the voids (or pores) 30 that are formed in the semiconductor surface with an -H atom and -OH group connected to the silicon (Si). The alkyl anneal occurs by the passivation anneal of the Si-OC surface layer as shown in FIG. 2. The plasma energy and heat induces the breaking of the appropriate bonds and the forming of the termination chemical species onto the Si-O-Si bonds with $(\text{CH}_3)_3$.

[0023] FIGS. 3 and 4 illustrate in schematic diagrams the use of hexamethyldisilane and methyltriacetoxysilane as the alkyl component, where the voids 30 having the Si-OH and SiH groups are replaced with an Si-O-Si and $\text{CH}_3(\text{CH}_3)_3$ or CH_3 groupings. Typically, the hexamethyldisilane and the methyltriacetoxysilane is at a concentration of about 1% to about 30% during the anneal passivation depending on the carbon content and other factors as determined by those skilled in the art.

[0024] FIG. 5 illustrates an example of a plasma enhanced chemical vapor deposition chamber 16 used with the present invention. A housing 40 is substantially

cylindrically configured and includes a centrally located housing extension 41 having a bore 42. The bore 42 contains a hollow drive spindle 44 with a circular configured wafer platen holder 46 that forms a substantially circular configured wafer holding top surface 48. A magnetic rotation drive 50 is operatively connected to the drive spindle 44 and rotates the wafer platen holder 46 as the drive 50 rotates the spindle 44. A power shielded radio frequency generator source 52 connects into an electrode 54 that extends through the top surface of the chamber 16 and provides the heating necessary to allow plasma generation within the chamber. A source of alkyl gas 60 provides an alkyl gas to the chamber, which is forced into the chamber 16 via a gas orifice 62 contained in the hollow drive spindle 44. Vacuum pumps 66 withdraw vacuum from the chamber 16. Heaters 70 are placed under the chamber 16 and also provide additional heat for heating the wafers W.

[0025] In operation, the wafers W formed of the substrate 10 and polysilicon-oxy-carbide surface layer 12 are placed onto the wafer platen holder 46. Gas flow in the form of the desired alkyl is forced upward through the drive spindle 44 into the chamber 16. The vacuum pump 66 also withdraws all ambient air from the chamber before gas flow. Wafers are initially heated through the heaters 70. The magnetic rotation drive 50 rotates the wafers W within the chamber and the power shielded RF generator 52 supplies the necessary power to the electrode 54 to form the plasma and allow the passivation layer to be formed as described before.

[0026] FIGS. 2-4 illustrate a semiconductor article that comprises a polysilicon-oxy-carbide surface layer 12 deposited over a substrate 10 where the surface layer 12 has a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0. A passivating surface layer 12a is formed on the polysilicon-oxy-carbide and has a terminating chemical species that is substantially free of hydroxyl and formed by heating the polysilicon-oxy-carbide substrate within the chemical vapor deposition chamber and contacting the substrate with an alkyl selected from the group consisting of: acetylene, methane, hexamethyldisilane and methyltriacetoxysilane to bond molecules via Si-O-Si chains and dehydroxylate the surface. The hexamethyldisilane and methyltriacetoxysilane are about 1% to about 30% concentration and are illustrated diagrammatically in FIGS. 3 and 4.

[0027] Many modifications and other embodiments of the invention will come to the mind of one skilled in the art having the benefit of the teachings presented in the foregoing descriptions and the associated drawings. Therefore, it is to be understood that the invention is not to be limited to the specific embodiments disclosed.

Claims

1. A method of treating a semiconductor surface layer on a semiconductor substrate, wherein the semiconductor surface layer comprises a deposited polysilicon-oxy-carbide surface layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0, the method comprising the steps of:

positioning the semiconductor substrate within a chemical vapor deposition chamber;

heating the semiconductor surface layer; and

annealing the semiconductor surface layer within an alkyl environment of the chemical vapor deposition chamber to passivate the surface by bonding with the silicon an attaching alkyl terminating chemical species on the surface to aid in dehydroxylating the surface.

2. A method according to Claim 1, wherein the step of heating further comprises the step of heating with a plasma within the chemical vapor deposition chamber.

3. A method according to Claim 2, and further comprising the step of heating with a plasma power of about 100 to about 500 watts.

4. A method according to Claim 1, and further comprising the step of heating the surface by generating a radio frequency induced current.

5. A method according to Claim 1, and further comprising the step of annealing within a vacuum environment of about 1 to about 10 Torr.

6. A method of treating a semiconductor surface layer on a semiconductor substrate, wherein the semiconductor surface layer comprises a deposited polysilicon-oxy-carbide layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0, the method comprising the steps of:

positioning the semiconductor substrate within a plasma enhanced, chemical vapor deposition chamber;

heating the semiconductor surface layer within the chemical vapor deposition chamber with a plasma and a radio frequency induced current of about 12 MHz to about 14 MHz; and

annealing the semiconductor surface layer

- within an alkyl environment of the chemical vapor deposition chamber to passivate the surface by bonding with the silicon an attaching alkyl terminating chemical species on the surface to aid in dehydroxylating the surface.
7. A method according to Claim 6, and further comprising the step of heating with a plasma power of about 100 to about 500 watts.
8. A method according to Claim 6, and further comprising the step of annealing within a vacuum environment of about 1 to about 10 Torr.
9. A method of treating a semiconductor surface layer deposited over a semiconductor substrate, wherein the semiconductor surface layer comprises a deposited polysilicon-oxy-carbide surface layer, the method comprising the steps of:
- positioning the semiconductor substrate within a chemical vapor deposition chamber;
 - heating the semiconductor surface layer; and annealing the semiconductor surface layer within an alkyl environment of the chemical vapor deposition chamber having one of either hexamethyldisilazane of about 1 to about 30% concentration or methyltriacetoxysilane of about 1 to about 30 percent concentration to passivate the semiconductor surface layer by bonding with the silicon an attaching alkyl terminating chemical species on the semiconductor surface layer to aid in dehydroxylating the surface.
10. A method according to Claim 9, wherein the semiconductor surface layer comprises a deposited polysilicon-oxy-carbide surface layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0.
11. A method according to Claim 9, wherein the step of heating further comprises the step of heating with a plasma within the chemical vapor deposition chamber.
12. A method according to Claim 11, and further comprising the step of heating with a plasma power of about 100 to about 500 watts.
13. A method according to Claim 9, and further comprising the step of heating the surface by generating a radio frequency induced current.
14. A method according to Claim 9, and further comprising the step of annealing within a vacuum environment of about 1 to about 10 Torr.
15. A semiconductor article comprising:
5 a semiconductor substrate and a deposited polysilicon-oxy-carbide surface layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0 and a passivating surface layer having a terminating chemical species that is substantially free of hydroxyl and formed by heating the polysilicon-oxy-carbide surface layer within a chemical vapor deposition chamber and contacting the surface layer with an alkyl to bond molecules via Si-O-Si chains to dehydroxylate the surface.
16. A semiconductor article comprising:
10 a semiconductor substrate and a deposited polysilicon-oxy-carbide surface layer having a carbon content ranging from about 5% to about 20% at the molecular level and a dielectric constant of about 2.5 to about 3.0 and a passivating surface layer having a terminating chemical species that is substantially free of hydroxyl and formed by heating the polysilicon-oxy-carbide surface layer within a chemical vapor deposition chamber and contacting the surface layer with an alkyl selected from the group consisting of: acetylene, methane, hexamethyldisilane and methyltriacetoxysilane to bond molecules via Si-O-Si chains to dehydroxylate the semiconductor surface layer.
17. A semiconductor article according to Claim 16,
15 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
18. A semiconductor article according to Claim 16,
20 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
19. A semiconductor article according to Claim 16,
25 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
20. A semiconductor article according to Claim 16,
30 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
21. A semiconductor article according to Claim 16,
35 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
22. A semiconductor article according to Claim 16,
40 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
23. A semiconductor article according to Claim 16,
45 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
24. A semiconductor article according to Claim 16,
50 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.
25. A semiconductor article according to Claim 16,
55 wherein said hexamethyldisilane and methyltriacetoxysilane are at about 1 to about 30 percent concentration during passivation.

FIG. 1

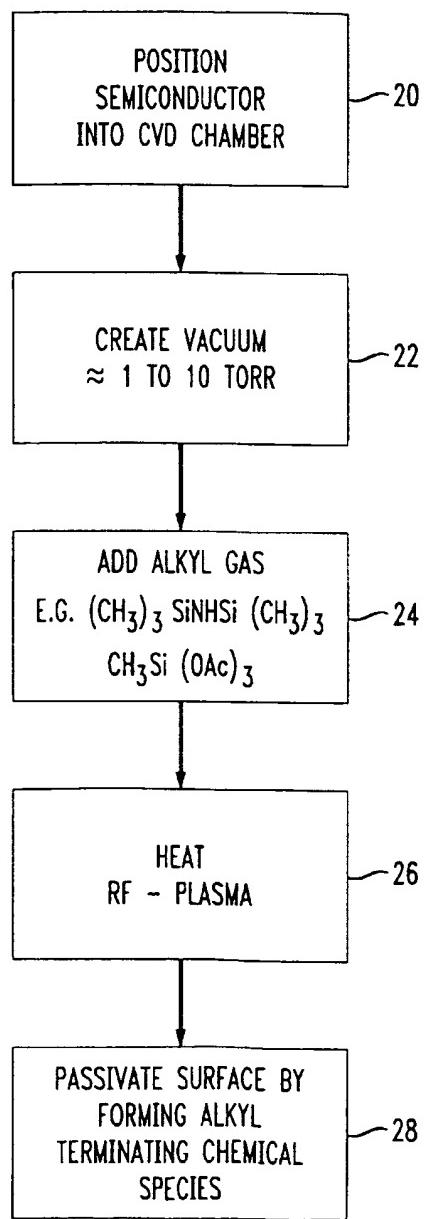


FIG. 2

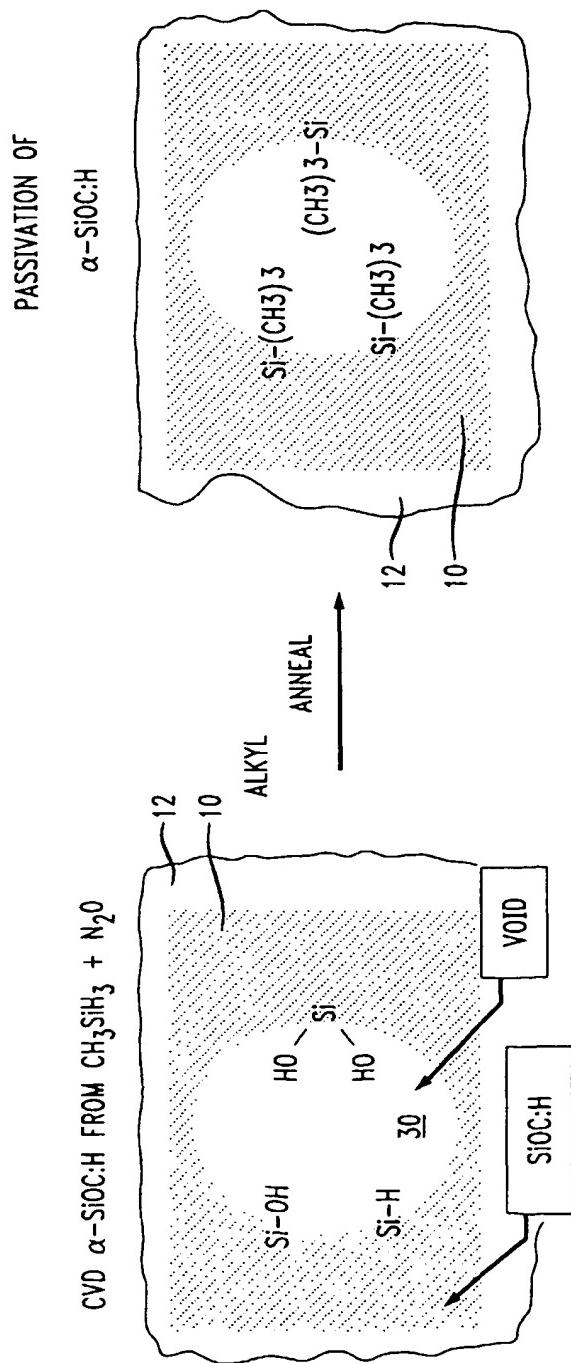


FIG. 3

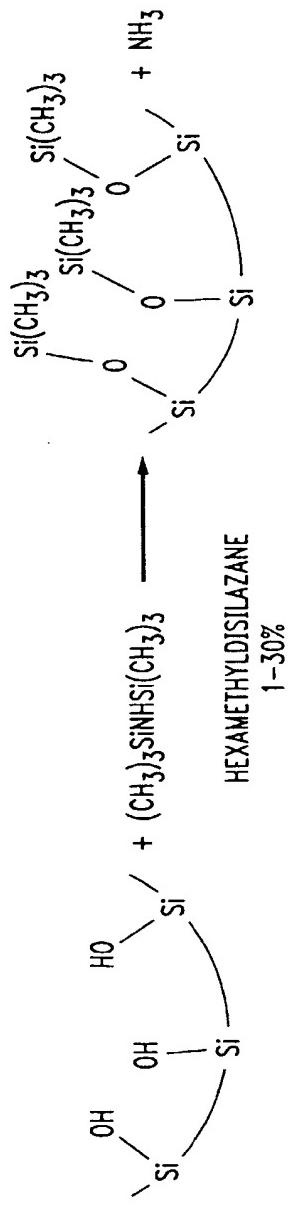


FIG. 4

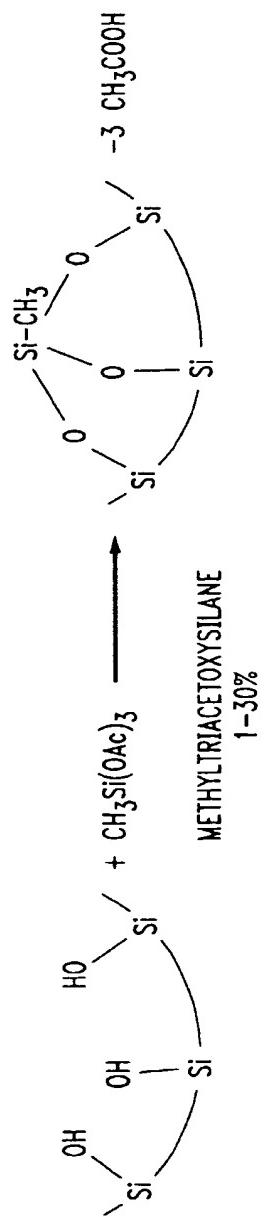
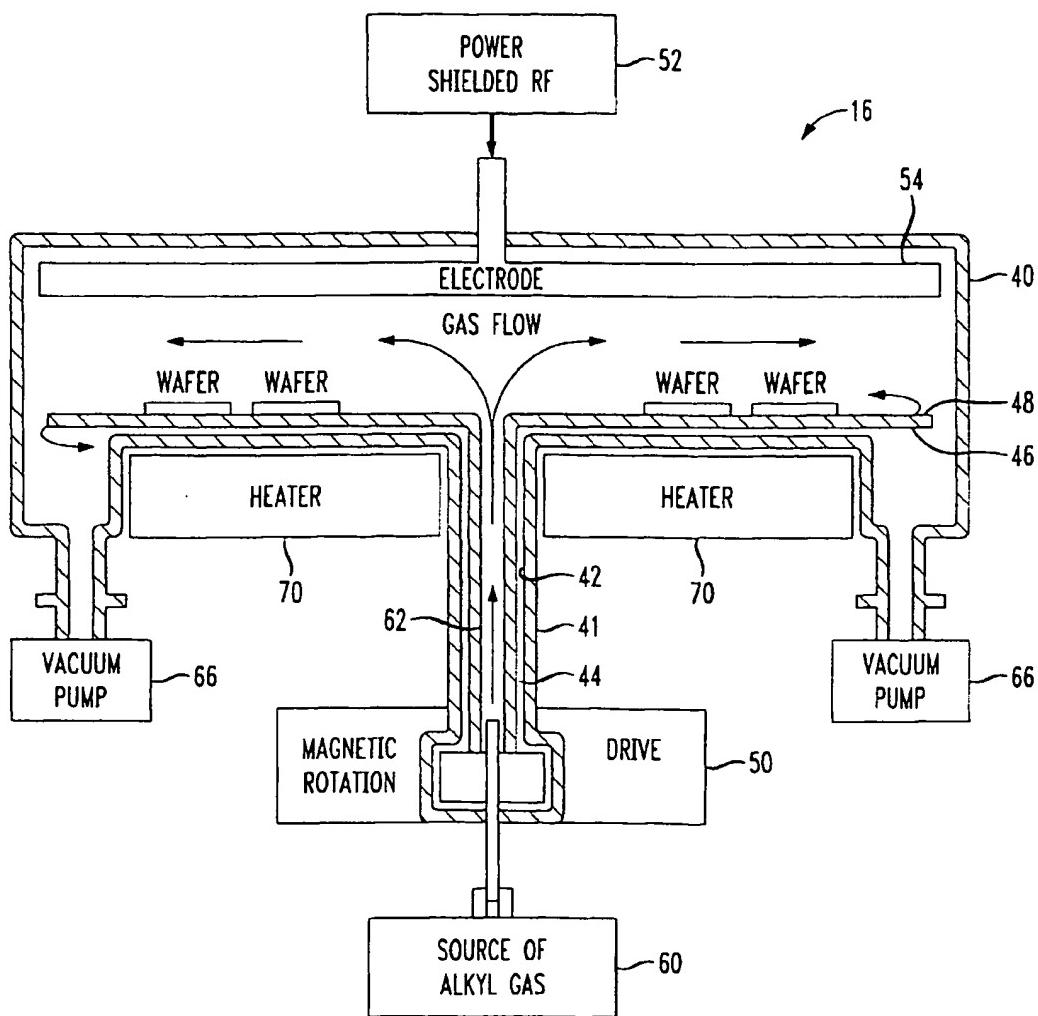


FIG. 5



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